

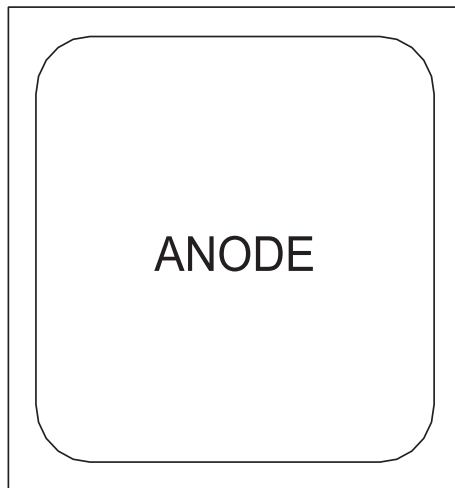
PROCESS CPD69
General Purpose Rectifier
1 Amp Glass Passivated Rectifier Chip



PROCESS DETAILS

Process	GLASS PASSIVATED MESA
Die Size	42.5 x 42.5 MILS
Die Thickness	12.5 MILS
Anode Bonding Pad Area	32 x 32 MILS
Top Side Metalization	Ni/Au - 5,000Å/2,000Å
Back Side Metalization	Ni/Au - 5,000Å/2,000Å

GEOMETRY



R0

GROSS DIE PER 4 INCH WAFER

6,200

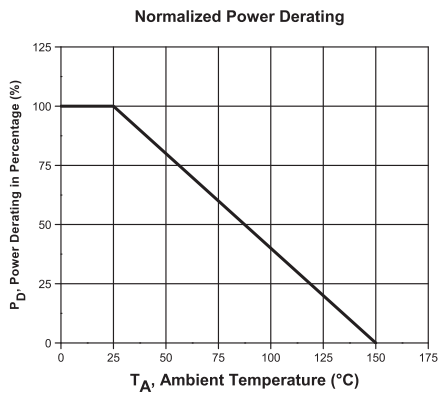
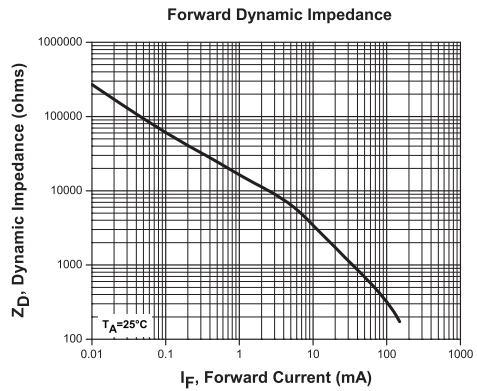
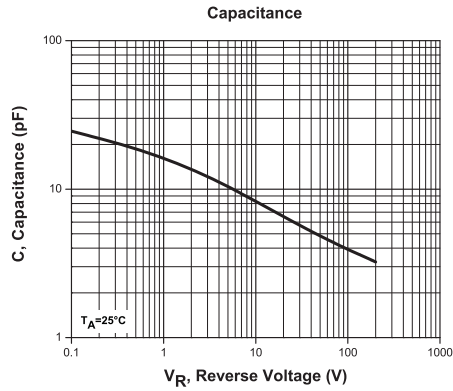
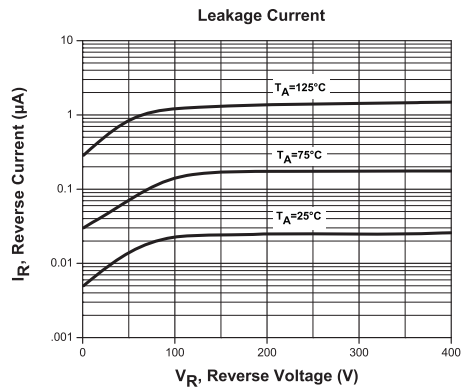
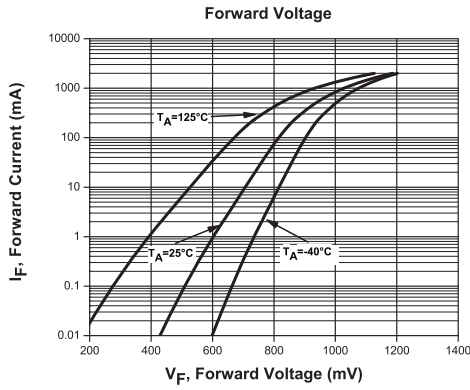
PRINCIPAL DEVICE TYPES

CMR1-02 Series
CMR1-02M Series
CXR1-04
CXR1-04C
CZR1-04
CZR1-04C

R5 (5-April 2011)

PROCESS CPD69

Typical Electrical Characteristics



R5 (5-April 2011)